

LL4150A

SILICON EPITAXIAL PLANAR DIODE

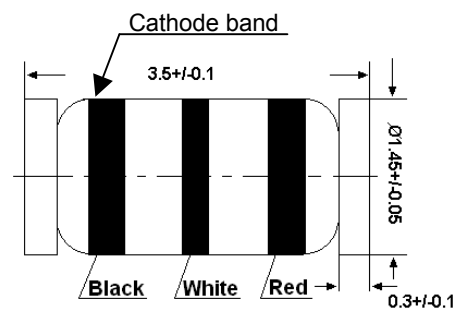
Features

- Fast Switching Speed
- High Reliability
- High Conductance
- For General Purpose Switching Applications

Mechanical Data

- **Terminals:** Solderable per MIL-STD-202, Method 208

LL-34



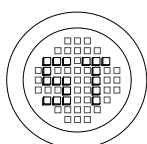
Glass case MiniMELF
Dimensions in mm

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristic	Symbol	Value	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	50	V
Forward Continuous Current (Note 1)	I_{FM}	400	mA
Average Rectified Output Current (Note 1)	I_O	300	mA
Power Dissipation (Note 1) Derate Above 25°C	P_{tot}	500 1.68	mW mW/ $^\circ\text{C}$
Junction temperature	T_J	200	$^\circ\text{C}$
Operating and Storage Temperature Range	T_{STG}	-65 to +175	$^\circ\text{C}$

Characteristics at $T_J = 25^\circ\text{C}$

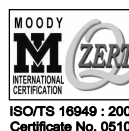
Characteristic	Symbol	Min.	Max.	Unit
Forward Voltage at $I_F = 300\text{mA}$	V_F	-	1.2	V
Peak Reverse Current at $V_R = 50\text{V}$	I_R	-	100	nA
Reverse Recovery Time at $I_F = I_R = 10$ to 200mA , to $0.1 I_F$	T_{RR}	-	4	nS



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